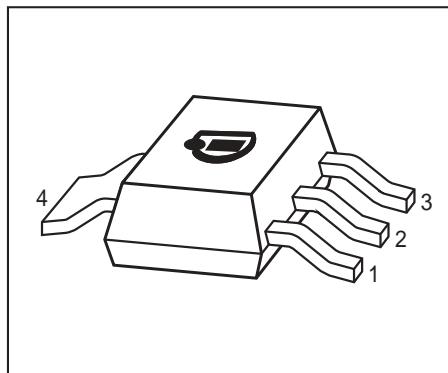


Silicon NPN Transistors

- For AF driver and output stages
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BDP948, BDP950 (PNP)



Type	Marking	Pin Configuration						Package
BDP947	BDP947	1=B	2=C	3=E	4=C	-	-	SOT223
BDP949	BDP949	1=B	2=C	3=E	4=C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage BDP947	V_{CEO}	45	V
BDP949		60	
Collector-base voltage BDP947	V_{CBO}	45	
BDP949		60	
Emitter-base voltage	V_{EBO}	5	
Collector current BDP947	I_C	3	A
BDP949		5	
Peak collector current	I_{CM}	200	mA
Base current BDP947	I_B	500	
Peak base current BDP949	I_{BM}	3	
Total power dissipation- $T_S \leq 99^\circ\text{C}$	P_{tot}	150	W
Junction temperature	T_j	-65 ... 150	
Storage temperature	T_{stg}		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 17	K/W

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$, BDP947 $I_C = 10 \text{ mA}, I_B = 0$, BDP949	$V_{(\text{BR})\text{CEO}}$	45 60	- -	- -	V
Collector-base breakdown voltage $I_C = 100 \mu\text{A}, I_E = 0$, BDP947 $I_C = 100 \mu\text{A}, I_E = 0$, BDP949	$V_{(\text{BR})\text{CBO}}$	45 60	- -	- -	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(\text{BR})\text{EBO}}$	5	-	-	
Collector-base cutoff current $V_{CB} = 45 \text{ V}, I_E = 0$ $V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	I_{CBO}	- -	- -	0.1 20	μA
Emitter-base cutoff current $V_{EB} = 4 \text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 2 \text{ A}, V_{CE} = 2 \text{ V}$	h_{FE}	25 85 50	- - -	- 475 -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 2 \text{ A}, I_B = 0.2 \text{ A}$	V_{CEsat}	-	-	0.5	V
Base emitter saturation voltage ¹⁾ $I_C = 2 \text{ A}, I_B = 0.2 \text{ A}$	V_{BEsat}	-	-	1.3	

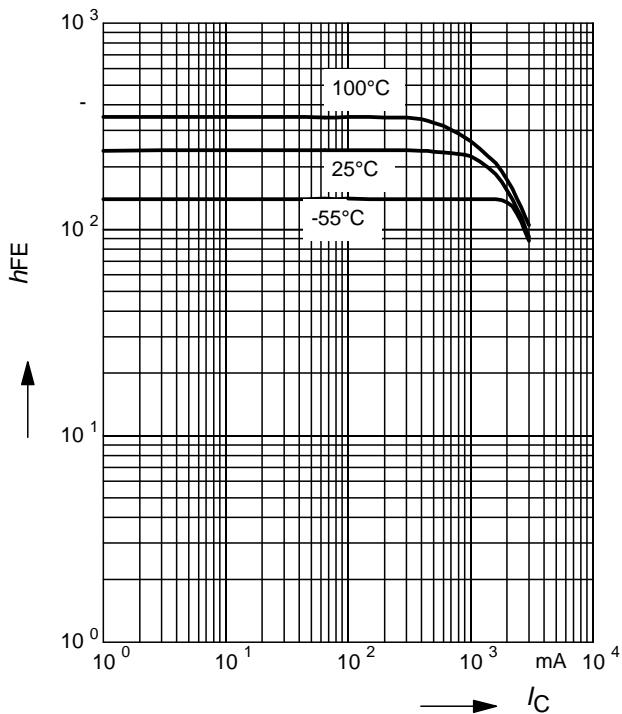
AC Characteristics

Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$	f_T	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	25	-	pF

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

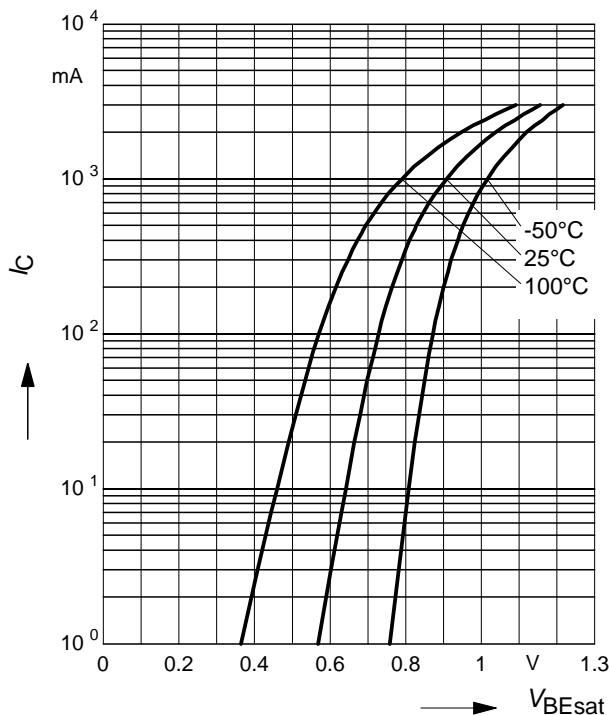
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 2 \text{ V}$$



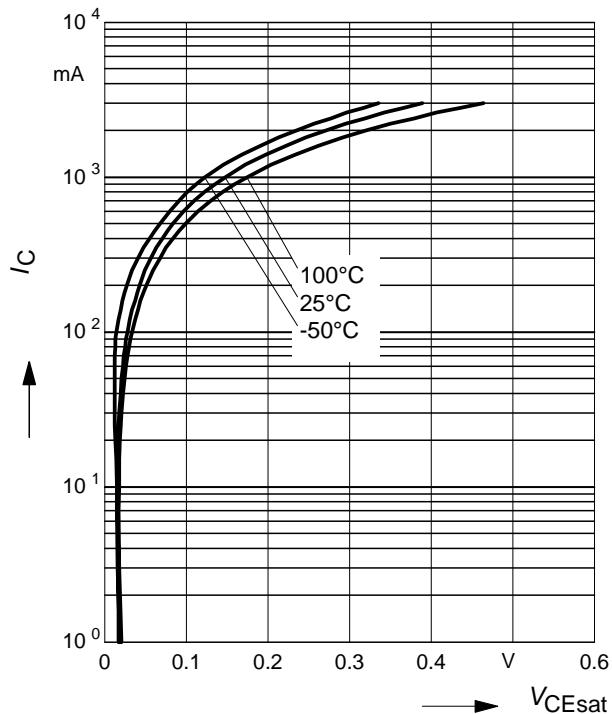
Base-emitter saturation voltage

$$I_C = f(V_{BEsat}), h_{FE} = 10$$



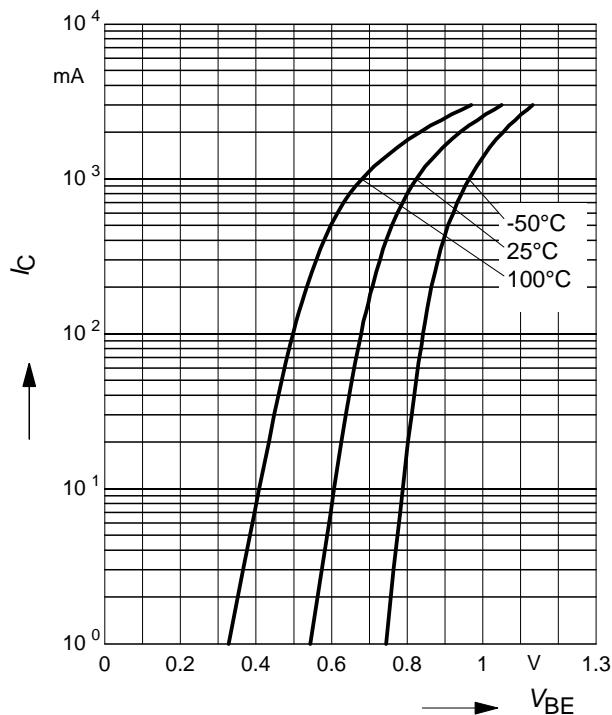
Collector-emitter saturation voltage

$$I_C = f(V_{CEsat}), h_{FE} = 10$$

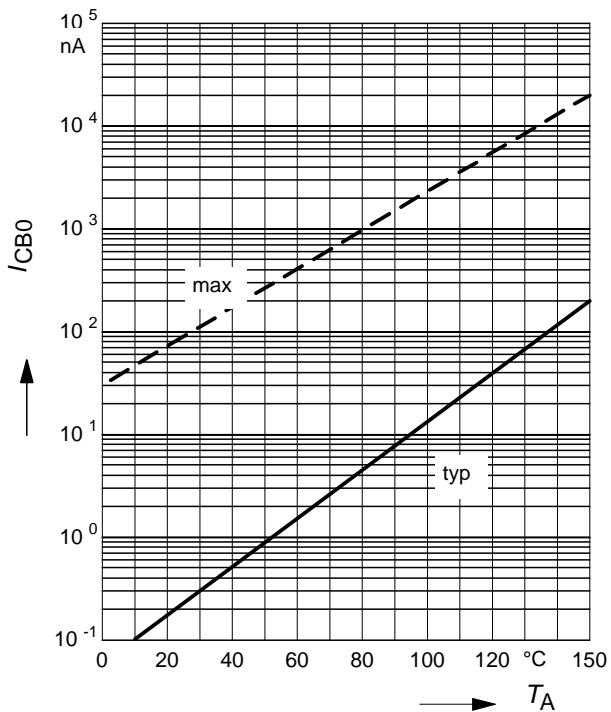


Collector current $I_C = f(V_{BE})$

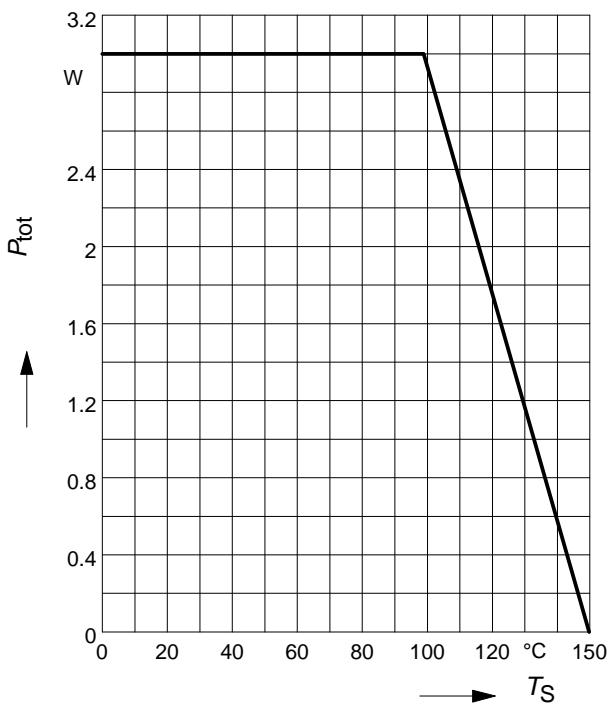
$$V_{CE} = 2 \text{ V}$$



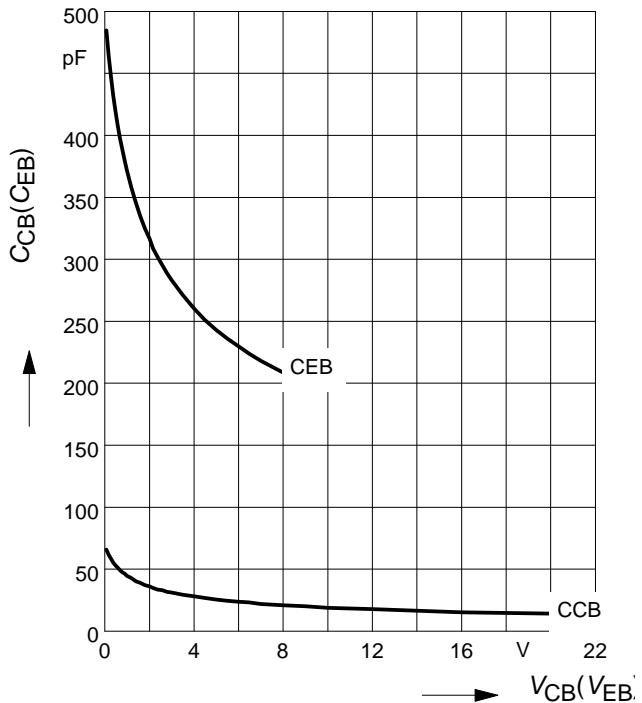
Collector cutoff current $I_{CBO} = f(T_A)$
 $V_{CB} = 45 \text{ V}$



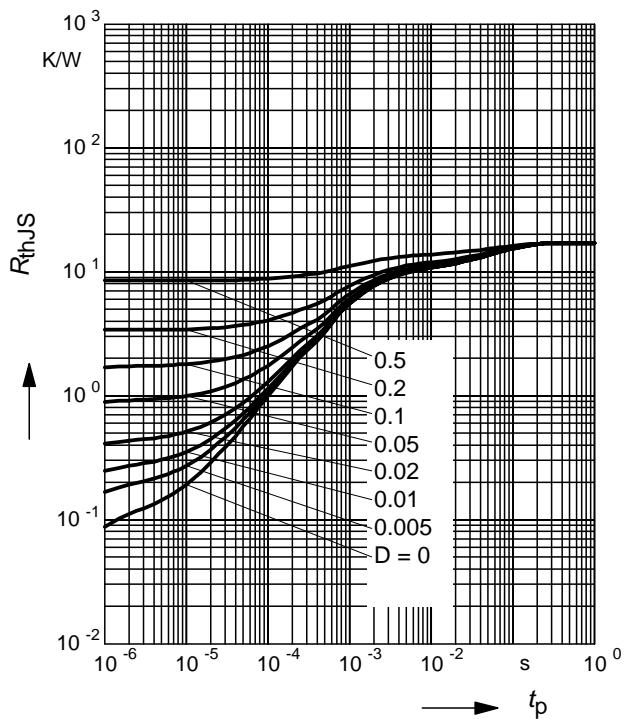
Total power dissipation $P_{\text{tot}} = f(T_S)$



Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$

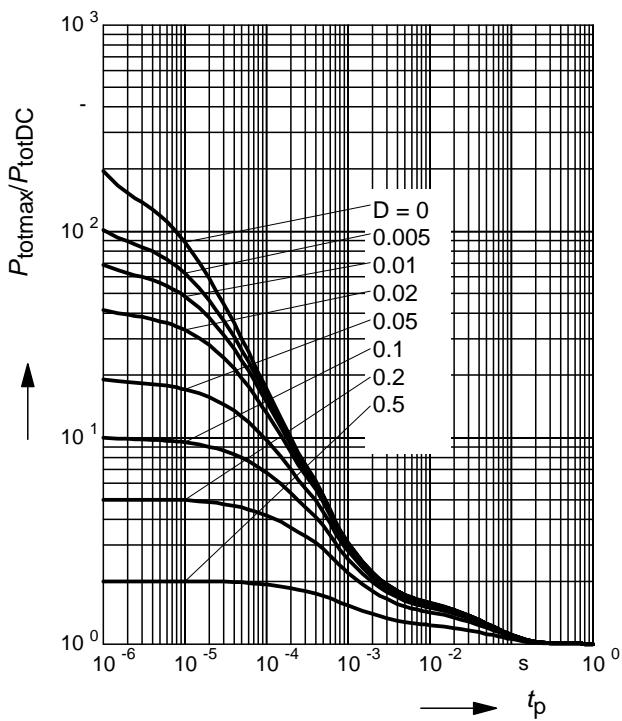


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

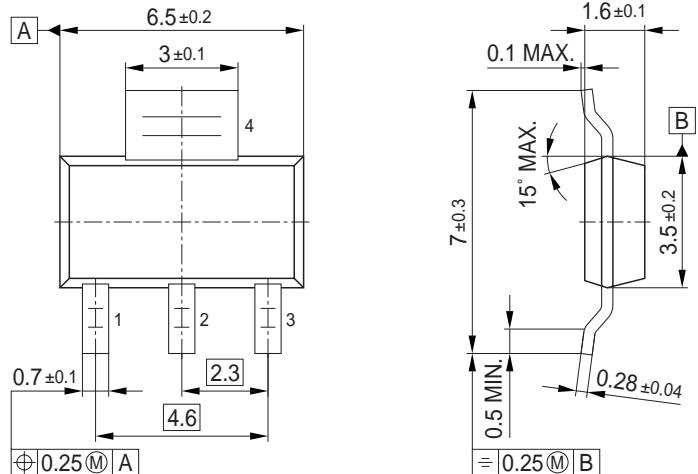


Permissible Pulse Load

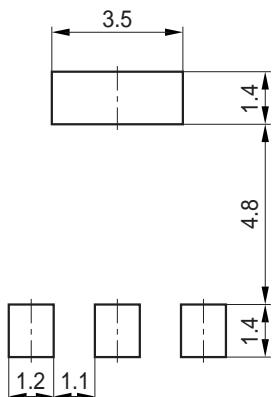
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



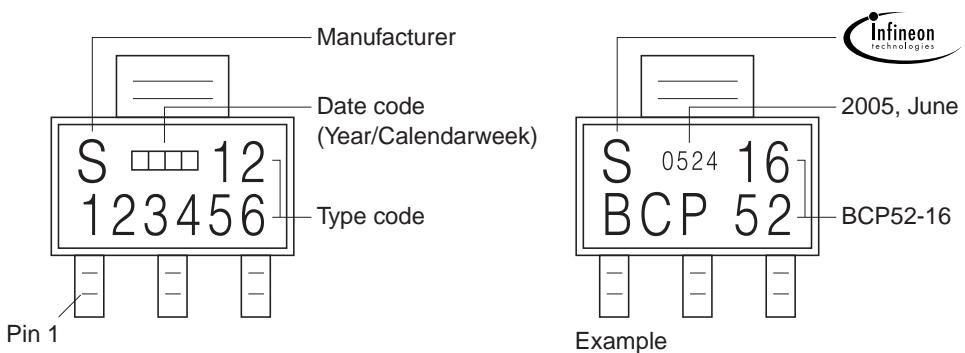
Package Outline



Foot Print

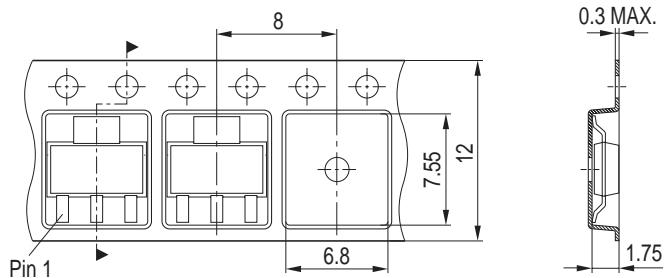


Marking Layout



Packing

Reel ø180 mm = 1.000 Pieces/Reel
Reel ø330 mm = 4.000 Pieces/Reel



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